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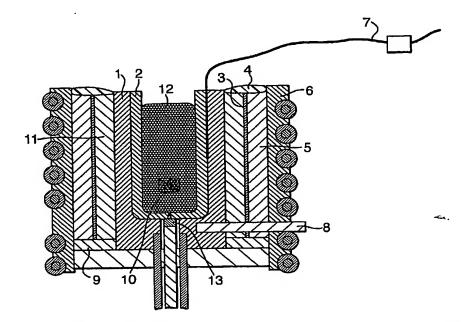
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(54) Title: NEW MATERIAL AND METHOD OF FABRICATION THEREFOR



(57) Abstract: The present invention concerns new methods of fabricating a silicon material comprising phosphorus. The methods allow high levels of phosphorus to be combined with the silicon. In one aspect of the invention a sample of phosphorus is surrounded with a sample of silicon. At least some of the phosphorus is then vaporised and caused to interact with the silicon.

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